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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTO	٦	ATTORNEY DOCKET NO.
09/298,160	04/22/99	CUSTER	D	MI22-1172
Г 021567		_ IM62/0515	7	EXAMINER
	OHN ROBERTS	GREGORY AND MATKIN	OLS	EN, A
SUITE 1300			ART UN	
601 W FIRS SPOKANE WA	T AVENUE 99201-3828	1	174	e 7
			DATE MAIL	.ED: 05/15/00

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks



Office Action Summary

Application No. 09/298,160

Applicant(s)

Custer et al.

Examiner

amıner Allan Olsen Group Art Unit 1746



X Responsive to communication(s) filed on Apr 22, 1999	
☐ This action is FINAL .	
Since this application is in condition for allowance except in accordance with the practice under <i>Ex parte Quayle</i> , 19	
A shortened statutory period for response to this action is see is longer, from the mailing date of this communication. Failulapplication to become abandoned. (35 U.S.C. § 133). Exter 37 CFR 1.136(a).	re to respond within the period for response will cause the
Disposition of Claims	
	is/are pending in the application.
Of the above, claim(s)	is/are withdrawn from consideration.
Claim(s)	is/are allowed.
	is/are rejected.
Claim(s)	is/are objected to.
	are subject to restriction or election requirement.
Application Papers See the attached Notice of Draftsperson's Patent Draw The drawing(s) filed on is/are objected to by the Examiner. The specification is objected to by the Examiner. The oath or declaration is objected to by the Examiner. Priority under 35 U.S.C. § 119 Acknowledgement is made of a claim for foreign prioric	ected to by the Examiner isapproveddisapproved
☐ All ☐ Some* ☐ None of the CERTIFIED copies☐ received. ☐ received in Application No. (Series Code/Serial N☐ received in this national stage application from the *Certified copies not received: ☐ All ☐ Some* ☐ None of the CERTIFIED copies of th	of the priority documents have been sumber) Humber) he International Bureau (PCT Rule 17.2(a)).
Attachment(s)	
 Notice of References Cited, PTO-892 ✓ Information Disclosure Statement(s), PTO-1449, Paper ☐ Interview Summary, PTO-413 ✓ Notice of Draftsperson's Patent Drawing Review, PTO- ☐ Notice of Informal Patent Application, PTO-152 	
SEE OFFICE ACTION O	N THE FOLLOWING PAGES

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Art Unit:

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371© of this title before the invention thereof by the applicant for patent.
- 2. Claims 1-5 are rejected under 35 U.S.C. 102(b) as being anticipated by US Patent 5,340437 issued to Erk et al. (hereinafter, Erk).

Erk teaches a method of etching and polishing semiconductor wafers that involves injecting a gas into an aqueous etchant. Erk's method includes an embodiment in which the injected gas is dissolved in the etchant until the saturation limit is reached. See: col. 3, lines 20-68; col. 7, lines 54-55; col. 8, lines 13-29 and 57-60.

3. Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by US Patent 4,817,652 issued to Liu et al. (hereinafter, Liu).

Liu teaches a method of cleaning semiconductor wafers that involves injecting a gas into an etchant. Liu does not explicitly teach what the concentration of the dissolved gas that is obtained by the method. However, the data provided by Liu shows that Liu has conducted

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studies at gas pressures as high as 1,680 psi. This high pressure would inherently produce a

solution having a dissolved gas concentration of at least 200 ppb. See col. 5, lines 13-25; col. 6,

lines 48-54; col. 7, lines 26-67.

Conclusion

4. The prior art made of record and not relied upon is considered pertinent to applicant's

disclosure. Each of US Patents: 5,800,626; 5,849,091; 5,858,106; 5,887,605; and 6,039,815

have teachings that provide the basis for a 102 rejection over independent claim 1, however, given

the above 102(b) rejections the examiner considers it unnecessary to make these additional

rejections at this time.

5. Any inquiry concerning this communication or earlier communications from the examiner

should be directed to Allan Olsen whose telephone number is (703) 306-9075. The examiner can

normally be reached on Monday through Friday from 9:30 to 6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor,

Randy Gulakowski, can be reached on (703) 308-4333. The fax phone number for this Group is

(703) 305-7719.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the Group receptionist whose telephone number is (703) 308-0661.

Allan Olsen, Ph.D.

May 8, 2000

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TECHNOLOGY CENTER 1700

	L #	Hits	Séarch Text
1	L1		dissolv\$ near gas\$
2	L2	34252	gasif\$ ozonated ozone adj water
3	L3	45037	1 2
4	L4	1806	3 and (216/\$.ccls. 134/\$.ccls. 438/\$.ccls. 252/\$.ccls. 137/\$.ccls. 239/\$.ccls. 451/\$.ccls.)
5	L 5	353	4 and semicon\$
6	L6	97	4 and polish\$
7	L7	251	(4 AND etch\$)
8	L8	309	4 and (dissolved adj gas\$)
9	ГЭ	45	8 and (polish\$ etch\$)
10	L11	33	9 and semicon\$

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